

FEATURES

- 45 mΩ High-Side MOSFET
- 0.5~4.0 A (typ.) Adjustable Current Limit
- 6.0mA Average Current in OUT shorted GND
- Support Apple® Devices fast charging (Apple® 2.1A / 2.4A mode)
- Support Samsung Galaxy Tab Devices fast Charging
- Support BC1.2 & YD/T 1591-2009 Charging Spec
- Linear Current sense of Output Current.
- Built-in Soft-Start
- Support single layer PCB layout.
- $4.5 \sim 6.5$ V Single Supply Operation.
- Available EMSOP8, ESOP8 package.

APPLICATIONS

- USB Charger
- USB Wall Adapter
- Car Charger

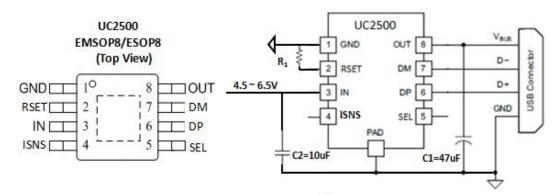
DESCRIPTION

The UC2500 integrated USB charger emulators with automatic host charger identification circuitry and high performance adjustable current limiting power switch. An automatic USB charger identification circuit allows mobile power supply can automatically provides the correct modes on the data lines to charger compliant devices among the Apple, Samsung and BC1.2 modes.

The UC2500 is a $45 m\Omega$ power switch intended for applications where heavy capacitive loads and short-circuits are likely to be encountered. This also provides hiccup mode when OUT voltage is less than 1.8V or OTSD.

The UC2500 provides a ISNS pin for current sense or USB cable resistance compensation and an SEL pin to select 10W or 12W mode in application.

PACKAGE AND APPLICATION



SEL = 0: Apple=2.4A, SS=2A, DCP=1.5A;

SEL = 1 or Floating: Apple=2.1A, SS=2A, DCP=1.5A;

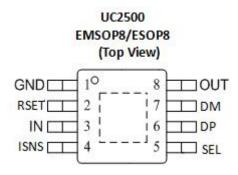
ISNS is floating or pull up with 10k Resistor if not used

ORDING information

Part Number	Package Type	Package Qty	Op Temp(°C)	Mark	
UC2500	EMSOP8	3000	-40~85	UC2500	
0C2300	ESOP8	3000	-40~83	XXX	



PINOUT



PIN FUNCTIONS

NO.	NAME	TYPE ⁽¹⁾	DESCRIPTION
1	GND	G	Ground connection
2	RSET	I	External resistor used to set current-limit threshold;
3	IN	P/I	Power supply/Input voltage connected to Power Switch; connect a 1 μF or greater ceramic capacitor from IN to GND as close to the IC as possible
4	ISNS	О	Current Sense of OUT current, the current sense ratio is 39uA/A;
5	SEL	I	Logic-level control input; When it is high or floating, DP/DM operate in 2.1A mode, when it is Low, DP/DM operate in 2.4A mode;
6	DP	O/I	DP date line to connector, output for hand-shake voltage to portable equipment, high impedance while disabled
7	DM	O/I	DM data line to connector, input for hand-shake voltage from portable equipment high impedance while disabled
8	OUT	О	Power-switch output, connected to VBUS of USB; connect a 22μF or greater ceramic capacitor from OUT to GND as close to the IC as possible

(1) G = Ground, I = Input, O = Output, P = Power

MARK INFORMATION



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ABSOLUTE MAXIMUM RATINGS (1)

Over recommended operating free-air temperature range (unless otherwise noted)

PAR	MIN	MAX	UNIT		
Supply Voltage Range	IN	-0.3	7.0	V	
Input voltage range	DP,DM	-0.3	5.8	v	
Continuous output sink current	DP input current, DM input current		35		
Continuous output source current	DP output current, DM output current		35	mA	
ECD C II D I M 11(III)	IN		2	137	
ESD rating, Human Body Model (HBM)	DP, DM		2	kV	
Operating Junction Temperature	T_J	-40	125	°C	
Storage Temperature Range T _{stg}		-65	150		

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

THERMAL METRIC				
0	EMSOP8 Package thermal impedance ⁽¹⁾	65	00/11	
$\theta_{ m JA}$	ESOP8 Package thermal impedance ⁽¹⁾	42	°C/W	

⁽¹⁾ The package thermal impedance is calculated in accordance with JESD 51-7.

RECOMMENDED OPERATING CONDITIONS

	PARAMETER	MIN	MAX	UNIT
V _{IN}	Input voltage of IN	4.5	6.5	V
V _{DP/DM}	DP data line input voltage		5.5	V
I _{DP/DM}	Continuous sink/source current		±10	mA
R _{SET}	Resistance of R _{SET}	13	100	kΩ
I _{OUT}	Continuous sink/source current	500	4000	mA
TJ	Operating Junction Temperature	-40	125	°C

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ELECTRICAL CHARACTERISTICS

Conditions are: TA = 25°C, VIN = 5.0 V, VSEL = VIN and RSET = 19.1 k Ω . Positive current are into pins. All voltages are with respect to GND (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Power Switch							
D	EMSOP8 Package			45	68		
R _{DSON}	ESOP8 Package	I _{OUT} =1A		55	83	mΩ	
	Curre	ent Limit					
Ios	OUT current limited	BIN1: R _{SET} =19.1k	2.45	2.74	3.03	A	
108	OO1 current minica	BIN2: R _{SET} =21.5k	2.45	2.74	3.03	A	
	Hicco	up Mode					
V _{OUT_SHORT}	OUT Threshold Voltage to enter Hiccup mode		1.3	1.50	1.7	V	
T _{ON_HICCUP}	ON Time of Hiccup mode		11	22	33	ms	
T _{OFF_HICCUP}	OFF Time of Hiccup mode		5	11.5	18	S	
	Curr	ent Sense					
		IOUT=3.0A		117			
I_{CS}	OUT current sense	IOUT=2.0A		78		uA	
		IOUT=1.0A		39			
Bandwidth				600		kHz	
	Thermal Shutdown						
	Temperature Rising Threshold		145	152	160	0.0	
	Hysteresis			17		°C	



ELECTRICAL CHARACTERISTICS

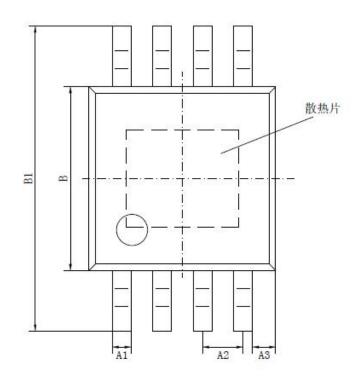
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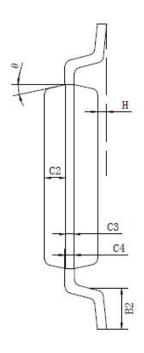
]	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	UNDERV	OLTAGE LOCKOUT		'		
V _{UVLO} IN rising UVLO threshold voltage 3.7				3.95	4.15	V
	Hysteresis			100		mV
	SUF	PPLY CURRENT				
I_{IN}	IN supply current			160	280	μΑ
	BC 1.2 D	OCP MODE (SHORT)				
R _{DPM_SHORT}	DP / DM shorting resistance			125	200	Ω
R _{DCHG_SHORT}	Resistors connected DP /DM to GND after hand-shaking			200	400	kΩ
V _{DPL_TH_DETACH}	DP low threshold while detaching BC1.2 devices		310	330	350	mV
Vdpl_th_detach_hys	hysteresis			50		mV
	IPAD MODE 2.	1A Mode (SEL=1 or Floa	ting)			
V_{DP_IPAD}	DP output voltage		2.5	2.7	2.9	V
V_{DM_IPAD}	DM output voltage		1.85	2.0	2.15	V
R_{DP_IPAD}	DP output impedance	$I_{DP} = -5uA$	20	30	40	kΩ
R_{DM_IPAD}	DM output impedance	$I_{DM} = -5uA$	20	30	40	kΩ
	IPAD MO	DE 2.4A Mode (SEL=0)				
$V_{ ext{DP_IPAD}}$	DP output voltage		2.5	2.7	2.9	V
V_{DM_IPAD}	DM output voltage		2.5	2.7	2.9	V
R_{DP_IPAD}	DP output impedance	$I_{DP} = -5uA$	20	30	40	kΩ
R _{DM_IPAD}	DM output impedance	$I_{DM} = -5uA$	20	30	40	kΩ
	Ga	laxy Tab MODE				
$ m V_{DP_GAL}$	DP output voltage		1.1	1.2	1.3	* 7
V_{DM_GAL}	DM output voltage		1.1	1.2	1.3	V
R_{DP_GAL}	DP output impedance	$I_{DP} = -5uA$	65	105	140	1.0
R _{DM_GAL}	DM output impedance	$I_{DM} = -5uA$	65	105	140	kΩ

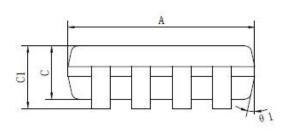


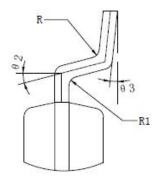
PACKAGE INFORMATION

EMSOP8





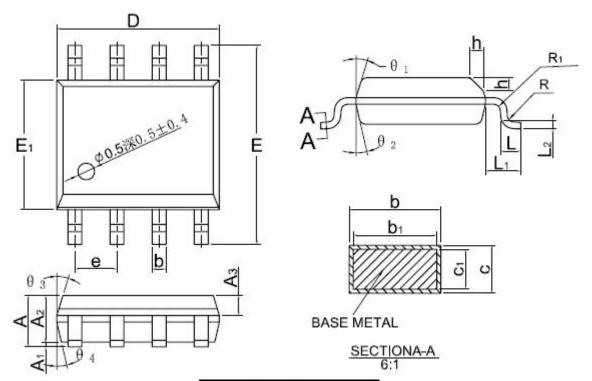




尺寸	最小(mm)	最大(mm)	标注	最小(mm)	最大(mm)
A	2. 90	3, 10	C3	0.	152
A1	0. 28	0. 35	C4	0.15	0.23
A2	0.6	5TYP	H	0.02	0.15
A3	0.3	75TYP	θ	12	° TYP4
В	2. 90	3. 10	θ 1	12° TYP4	
B1	4.70	5. 10	θ 2	14° TYP	
B2	0.45	0. 75	θ 3	0° ~ 6°	
С	0.75	0.95	R	0. 15TYP	
C1	9 7.	1. 10	R1	0. 15TYP	
C2	0.3	28TYP			



ESOP8



SYMBOL	MIN	NOM	MAX
Α	1.35	1.55	1.75
A ₁	0.00		0.10
A ₂	1.25	1.40	1.65
A ₃	0,50	0,60	0.70
b	0.39	_	0.49
b ₁	0.28	\mathcal{F}	0.48
С	0,10	\rightarrow	0,25
C1	0.10		0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
Ę	3,80	3.90	4.00
е		1.27BSC	
L	0.45		1.00
L ₁		1,04REF	
L2		0.25BSC	
R	0,07		1
R ₁	0.07	-	1
h	0,3	0.4	0,5
	0°	_	8°
0	11°	17°	19°
0 1	11°	13°	15°
0 1	15°	17°	19°
0	11°	13°	15°
EP1	2.40		
EP2	3.30	 -	